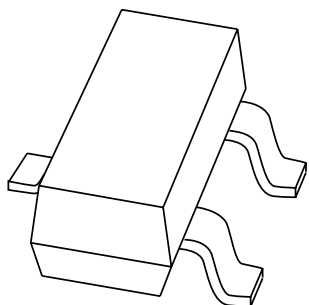


DATA SHEET



BC859; BC860 PNP general purpose transistors

Product specification
Supersedes data of September 1994
File under Discrete Semiconductors, SC04

1997 May 26

PNP general purpose transistors

BC859; BC860

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

APPLICATIONS

- Low noise input stages of audio frequency equipment.

DESCRIPTION

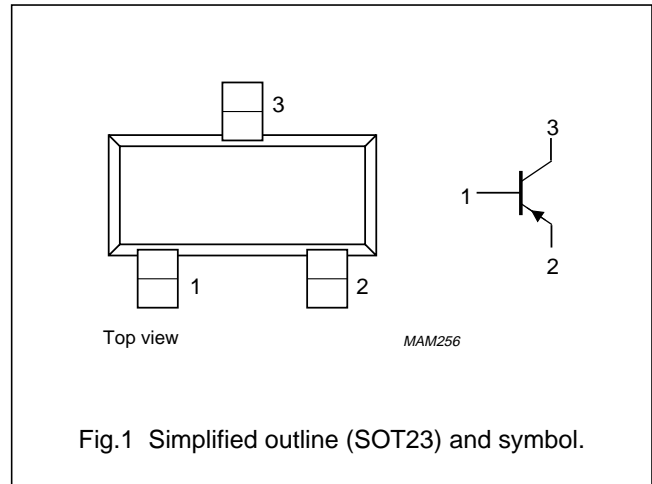
PNP transistor in a SOT23 plastic package.
NPN complements: BC849 and BC850.

MARKING

TYPE NUMBER	MARKING CODE	TYPE NUMBER	MARKING CODE
BC859	4Dp	BC860	4Hp
BC859A	4Ap	BC860A	4Ep
BC859B	4Bp	BC860B	4Fp
BC859C	4Cp	BC860C	4Gp

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BC859		–	–30	V
	BC860		–	–50	V
V _{CEO}	collector-emitter voltage	open base			
	BC859		–	–30	V
	BC860		–	–45	V
I _{CM}	peak collector current		–	–200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 60 °C	–	250	mW
h _{FE}	DC current gain	I _C = –2 mA; V _{CE} = –5 V	125	800	
f _T	transition frequency	I _C = –10 mA; V _{CE} = –5 V; f = 100 MHz	100	–	MHz

PNP general purpose transistors

BC859; BC860

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BC859		–	–30	V
	BC860		–	–50	V
V _{CEO}	collector-emitter voltage	open base			
	BC859		–	–30	V
	BC860		–	–45	V
V _{EBO}	emitter-base voltage	open collector	–	–5	V
I _C	collector current (DC)		–	–100	mA
I _{CM}	peak collector current		–	–200	mA
I _{BM}	peak base current		–	–200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

PNP general purpose transistors

BC859; BC860

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

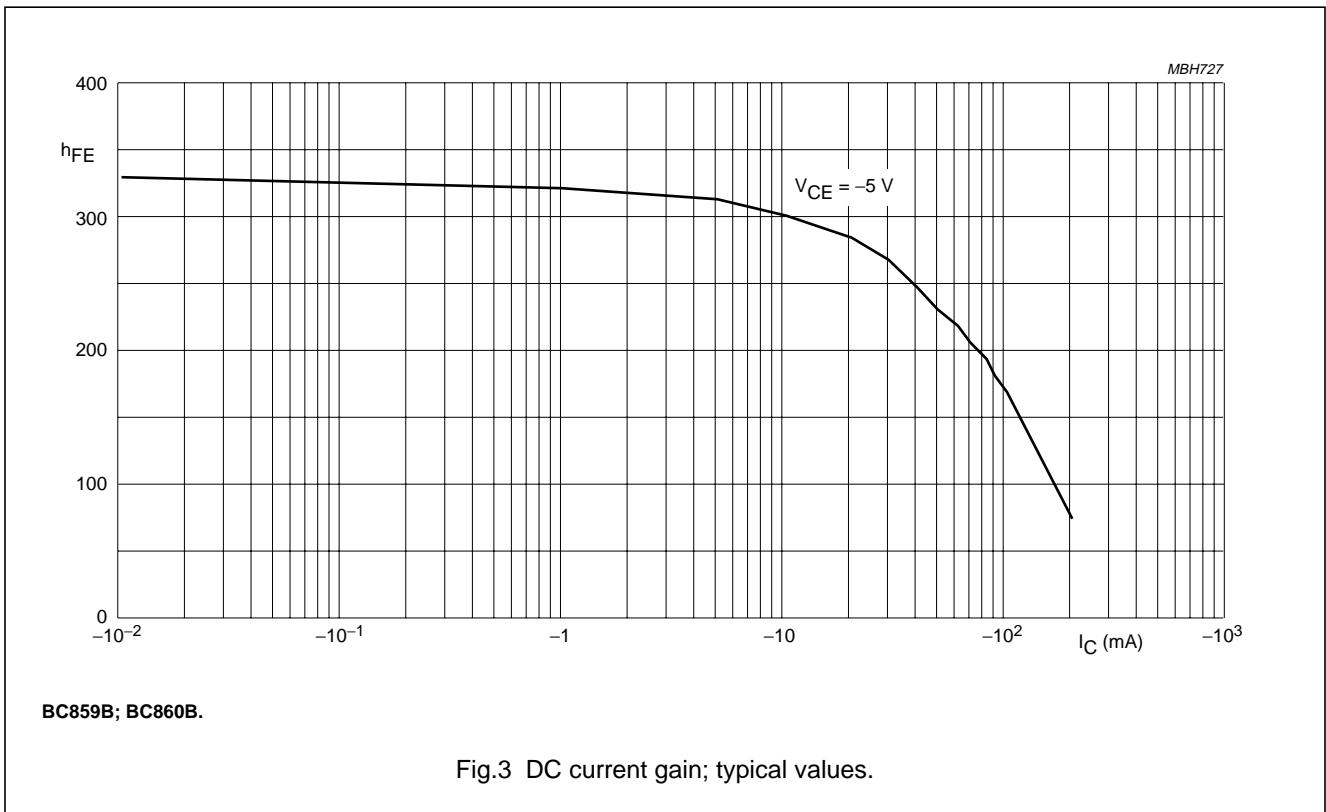
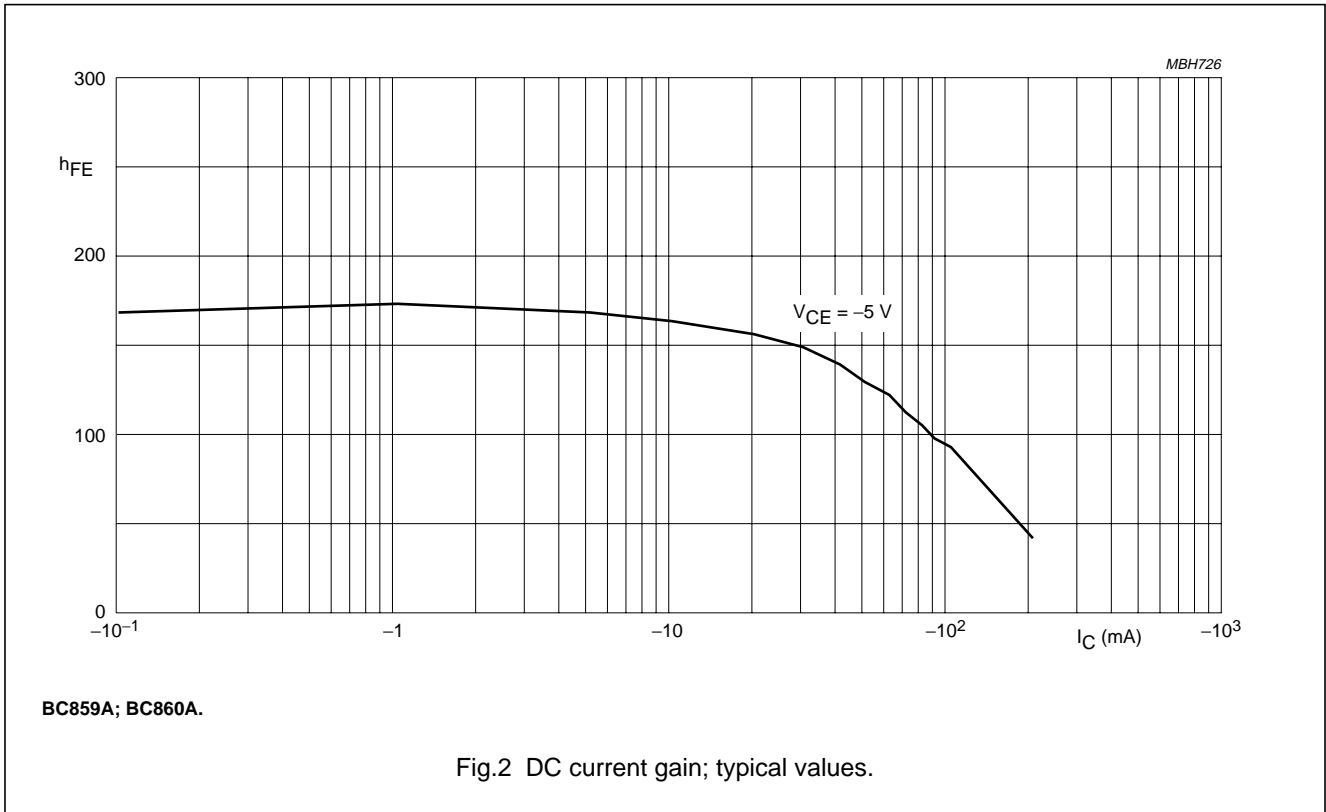
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -30\text{ V}$	–	–1	–15	nA
		$I_E = 0; V_{CB} = -30\text{ V}; T_j = 150\text{ °C}$	–	–	–4	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–	–100	nA
h_{FE}	DC current gain	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$	125	–	800	
h_{FE}	DC current gain BC859A; BC860A BC859B; BC860B BC859C; BC860C	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V};$ see Figs 2, 3 and 4	125	–	250	
			220	–	475	
			420	–	800	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	–	–75	–300	mV
		$I_C = -100\text{ mA}; I_B = -5\text{ mA}$	–	–250	–650	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA};$ note 1	–	–700	–	mV
		$I_C = -100\text{ mA}; I_B = -5\text{ mA};$ note 1	–	–850	–	mV
V_{BE}	base-emitter voltage	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V};$ note 2	–600	–650	–750	mV
		$I_C = -10\text{ mA}; V_{CE} = -5\text{ V};$ note 2	–	–	–820	mV
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	4.5	–	pF
C_e	emitter capacitance	$I_C = i_c = 0; V_{EB} = -500\text{ mV}; f = 1\text{ MHz}$	–	10	–	pF
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure BC859A; BC860A BC859B; BC860B BC859C; BC860C	$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 30\text{ Hz to }15\text{ kHz}$	–	–	10	dB
			–	–	4	dB
			–	–	–	–
F	noise figure BC859A; BC860A BC859B; BC860B BC859C; BC860C	$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	–	–	10	dB
			–	–	4	dB
			–	–	–	–

Notes

- V_{BEsat} decreases by about -1.7 mV/K with increasing temperature.
- V_{BE} decreases by about -2 mV/K with increasing temperature.

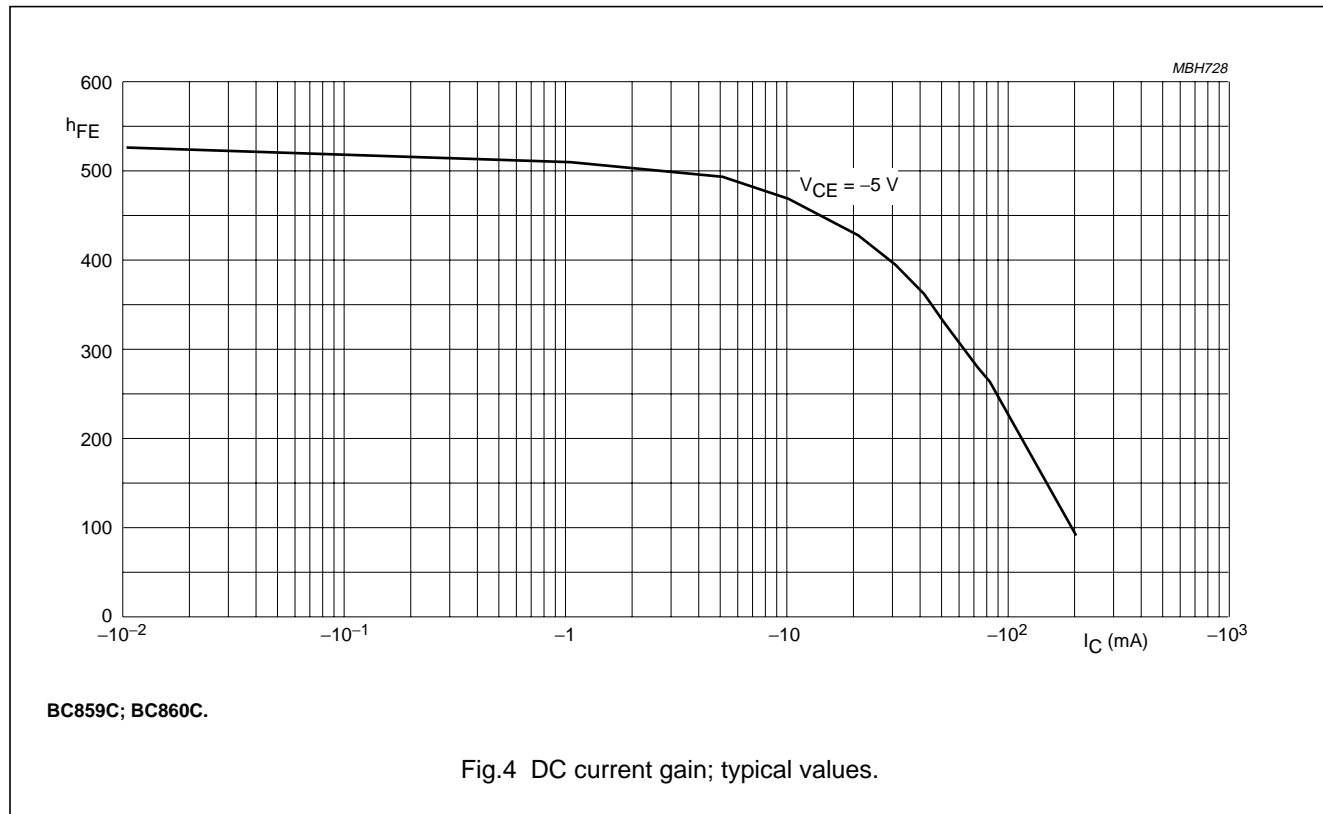
PNP general purpose transistors

BC859; BC860



PNP general purpose transistors

BC859; BC860



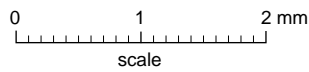
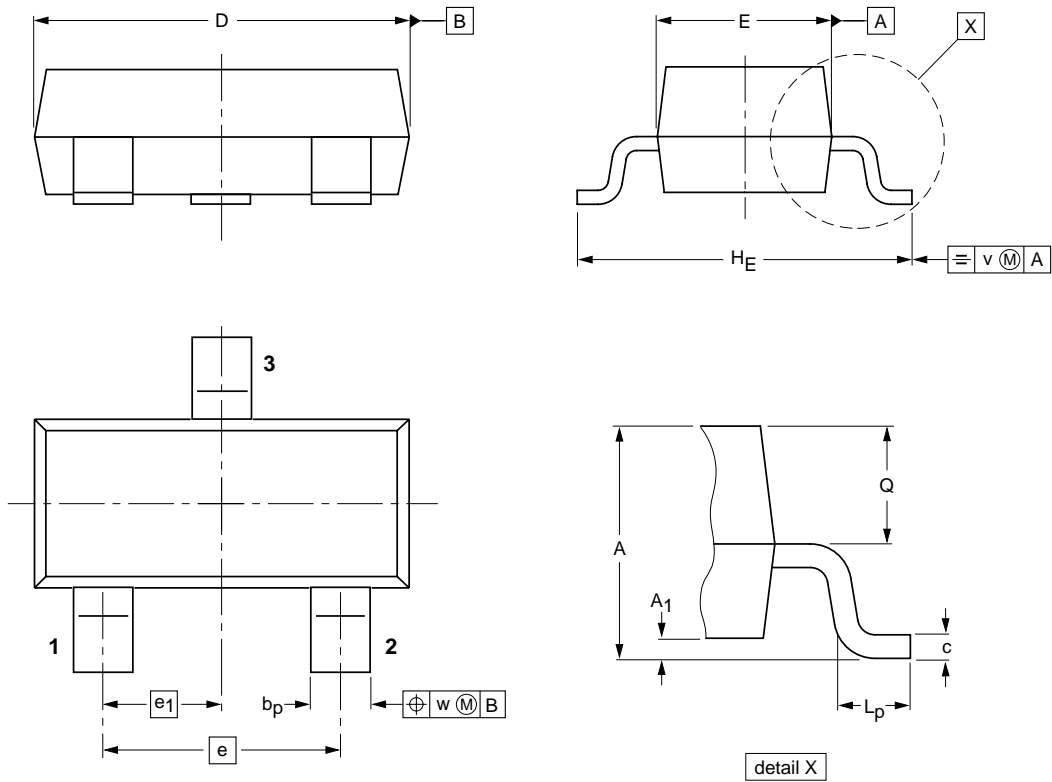
PNP general purpose transistors

BC859; BC860

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23						97-02-28

PNP general purpose transistors

BC859; BC860

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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PNP general purpose transistors

BC859; BC860

NOTES

PNP general purpose transistors

BC859; BC860

NOTES

PNP general purpose transistors

BC859; BC860

NOTES

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